

PREPARATION AND CHARACTERIZATION OF SOME
SEMICONDUCTING LAYERS USED IN SOLAR ENERGY FIELD
BY SPRAY PYROLYSIS TECHNIQUE.

THESIS
IN PARTIAL FULFILMENT FOR THE REQUIREMENTS
OF
THE MASTER OF SCIENCE DEGREE
IN PHYSICS



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1993



ACKNOWLEDGEMENTS

I would like to express my deepest feeling of gratitude and appreciation to those who supervised my work:

1. *Prof. Dr. Mansour Mohamed Hassab EI-Nabi*: Physics Department, Faculty of Girls, Ain-Shams University.
2. *Prof. Dr. Hassan Hassan Afifi*: Solid State Physics Department, National Research Centre.
3. *Dr. Salama Edward Demian*: Solid State Physics Department, National Research Centre.



CONTENTS

<i>SUBJECT</i>	<i>PAGE NO</i>
ACKNOWLEDGEMENTS	
ABSTRACT	i
SUMMARY	ii
CHAPTER I	
INTRODUCTION	1
1.1. AIM OF THE PRESENT WORK	4
CHAPTER II	
LITERATURE SURVEY	5
2.1. ZINC OXIDE REVIEW	5
2.2. FILM PREPARATION TECHNIQUES	15
CHAPTER III	
EXPERIMENTAL TECHNIQUE AND MEASUREMENTS	28
3.1. SPRAY PYROLYSIS SET-UP	28
3.2. CHOICE OF CHEMICALS USED FOR PREPARING ZnO FILMS AND THEIR CONCENTRATIONS	31
3.3. SPRAY PYROLYSIS TECHNIQUE PARAMETERS	32
3.3.1. SUBSTRATE TEMPERATURE AND DEPOSITION TIME	33
3.3.2. CARRIER GAS FLOW RATE	35
3.3.3. DOPING MATERIAL AND ITS CONCENTRATION	35

3.4.	FILM PREPARATION PROCEDURE	35
3.5.	PHYSICAL MEASUREMENTS	36
3.5.1.	STRUCTURAL MEASUREMENTS	36
	X-RAY DIFFRACTION AND SEM	
3.5.2.	OPTICAL MEASUREMENTS	37
3.5.3.	ELECTRICAL AND HALL MEASUREMENTS	41
CHAPTER IV		
	RESULTS AND DISCUSSION OF PURE AND DOPED ZINC OXIDE	44
4.1.	STRUCTURAL STUDIES	44
4.2.	OPTICAL RESULTS	53
4.2.1.	DETERMINATION OF FILM THICKNESS	55
4.2.2.	DETERMINATION OF OPTICAL CONSTANTS	
	$n, K, \text{AND } \alpha$	63
4.2.3.	DIELECTRIC PARAMETERS ϵ' AND ϵ''	72
4.2.4.	THE EFFECT OF INDIUM DOPING ON ZnO FILMS	75
4.3.	ELECTRICAL MEASUREMENTS	78
4.3.1.	ELECTRICAL CONDUCTIVITY σ	79
4.3.2.	HALL COEFFICIENT, NUMBER OF CARRIERS AND	
	THE EFFECT OF INDIUM DOPING	82
4.3.3.	THE HALL MOBILITY	83
	CONCLUSIONS	86
	APPENDIX I	88
	REFERENCES	93
	ARABIC SUMMARY	

LIST OF TABLES

<i>TABLE NO.</i>		<i>PAGE NO.</i>
TABLE 2.1.	The currently used solvents with their surface tension and viscosity values.	26
TABLE 4.1.	Lattice parameters.	45
TABLE 4.2.	The thickness of undoped and doped ZnO films.	57
TABLE 4.3.	The electrical parameters of ZnO doped 2% In, at two deposition times 50 and 70 minutes. . .	78

LIST OF FIGURES

<i>FIGURE NO.</i>		<i>PAGE NO.</i>
FIGURE 2.1.	Schematic diagram of the spray process	23
FIGURE 3.1.	The schematic diagram of the spray system.	29
FIGURE 3.2.	Description of the deposition initiated with increasing substrate temperature.	34
FIGURE 3.3.	(a) Holder for Hall voltage and sheet resistance measurements. (b) The sample between the magnet poles.	42
FIGURE 4.1a.	The X-ray diffraction pattern of ZnO films prepared at different substrate temperatures.	46
FIGURE 4.1b.	The effect of the substrate temperature on the peak profile of the diffraction planes.	48
FIGURE 4.2a.	The scanning electron microscope for as-deposited undoped ZnO films.	51
FIGURE 4.2b.	The scanning electron microscope for as-deposited doped ZnO films at 2% indium.	52
FIGURE 4.3.	The transmission curve for the glass substrate with air as a reference.	54
FIGURE 4.4.	The effect of the substrate temperature T_s on the $T-\lambda$ curves for undoped ZnO films.	56
FIGURE 4.5a.	The effect of the substrate temperature on the film thickness of the doped ZnO films.	59

FIGURE 4.5b.	The effect of the substrate temperature on the thickness of the ZnO films doped 2% In.	60
FIGURE 4.6a.	The effect of the spray time on the thickness of the undoped ZnO films.	61
FIGURE 4.6b.	The effect of the spray time on the thickness of the ZnO films doped 2% In.	62
FIGURE 4.7a.	The refractive index n against λ , for undoped ZnO films, at different substrate temperatures.	64
FIGURE 4.7b.	The refractive index n against λ , for doped ZnO films, at different substrate temperatures.	65
FIGURE 4.8.	The extinction coefficient k against λ for doped and undoped ZnO films.	66
FIGURE 4.9.	The absorption coefficient α against λ for undoped and doped ZnO films.	67
FIGURE 4.10.	The relation between $\text{Log}(\alpha)$ against the photon energy $h\nu$, for undoped ZnO films.	68
FIGURE 4.11.	The relation between $\text{Log}(\alpha)$ against the photon energy $h\nu$, for doped ZnO films.	70
FIGURE 4.12.	The calculated reflectivity against λ	71
FIGURE 4.13a.	The dielectric function (real part) against the photon energy $h\nu$, for undoped and doped ZnO films.	73

FIGURE 4.13b.	The dielectric function (imaginary part) against the photon energy $h\nu$, for undoped and doped ZnO films.	74
FIGURE 4.14.	The effect of the substrate temperature T_s , on the $T-\lambda$ curves, for doped ZnO films.	77
FIGURE 4.15.	The relation between the sheet resistance and the substrate temperature.	80
FIGURE 4.16.	The resistivity (Ω cm) against the substrate temperature.	81
FIGURE 4.17.	the number of free carriers, as a function of the substrate temperature.	84
FIGURE 4.18.	The mobility, as a function of the substrate temperature.	85

ABSTRACT

Pure and indium doped thin films of zinc oxide, had been prepared by spray pyrolysis technique. The substrate temperature was varied from 350-550 °C. Also, the deposition time was varied from 20 to 80 minutes, at each substrate temperature.

The structural, optical, and electrical properties for the prepared films, are measured as a function of substrate temperature, and deposition time.

SUMMARY

The electrical, optical and structural properties of Zinc Oxide thin films in the thickness range 50-370 nm deposited on glass substrates have been investigated. The films were prepared by using a non-conventional preparation technique. It is called spray pyrolysis technique. It permits deposition on either insulating or conducting substrates with a high degree of control over both the dimensions of the coatings and their physical properties.

The prepared film is controlled by many parameters such as: substrate temperature, deposition time, solution concentration, gas flow rates, and doping material. These parameters influence the structural, optical and electrical properties of the prepared ZnO films.

All these parameters have been tested. Testing many different solution concentrations and gas flow rates, showed that a satisfactory homogeneity, durability, reproducibility, and measurable electrical properties have been obtained at concentration 0.2 M, and 6 l/min. gas (filtered air) flow rate.

The deposition time was varied from 20-80 minutes at each substrate temperature ranging from 350-550 °C.

The effect of different substrate temperatures as well as deposition time on structural, optical and electrical properties have been studied.

Also, the preparation of films from aqueous solution of zinc acetate or zinc chloride, showed that the best ZnO films are obtained by using aqueous solution of zinc acetate.

X-ray diffraction patterns for the prepared zinc oxide films show that they are polycrystalline zinc oxide. The calculated lattice parameters are found to be very close to standard values of the hexagonal form of ZnO. The calculated crystallite size shows a nearly linear increase with the film thickness.

An analysis is carried out for the preferred orientation planes. The results reveal the existence of the preferred [002] orientation with the c-axis at high substrate temperatures.

Surface topography of some ZnO films have been investigated using SEM. Normally, indium-doped zinc oxide films have a smooth surface. In contrast, the undoped ZnO films have a much rougher surface than the doped ones. This implies that the presence of indium dopant atoms possibly affects the nucleation process of these films. These investigations agreed with that reported in literatures.

The measured optical transmission spectra, show high transparency of the film (90-95% transmission) in the visible range, with a sharp absorption edge around 375 nm wavelength which closely corresponds to the intrinsic band gap of ZnO (3.3 eV).

The optical constants n , k as well as film thickness have been calculated from the $T - \lambda$ curves. The thickness of the films was measured by etching half of the film area using dilute HCl as etchant. The height of the resulting step was measured using a height measuring instrument (Talystep). Measurements were carried out on some films whose thicknesses had been calculated from $T - \lambda$ curves. It is found that the measured values are consistent with those calculated from $T - \lambda$ curves.

The resistivity of the prepared doped zinc oxide films was found to change from 10^{-2} to 10^{-4} Ω cm, as the substrate temperature changes from 350-450 $^{\circ}$ C. This decrease may be due to the amelioration in crystallinity, grain size and current-carriers mobility.

The resistivity shows a considerable increase with increasing substrate temperature from 450 to 550 $^{\circ}$ C. This may be due to the recombination of the diffused alkali ions, from the substrate, with the free carriers.

The current carrier concentration was calculated from the Hall coefficient measurement. The obtained values are slightly dependent on substrate temperature in indium-doped films. The room-temperature Hall mobility μ ranged from 0.4 to 13 $\text{cm}^2/\text{V.S.}$ as the substrate temperatures varied from 350 to 550 $^\circ\text{C}$. This may be due to the increase in crystallinity and grain size.

The prepared pure and indium doped zinc oxide thin films show, generally, wide energy gap (3.3 eV), so it allows high transmission (90-95%) in the luminous solar range. Therefore, this material could be used as a window in heterojunction solar cells such as ZnO/CdTe. The obtained refractive index (2-1.75) values are in the right range, as to form an anti-reflection coatings on silicon solar cells. High conductivity ($5 \times 10^4 \Omega^{-1} \text{cm}^{-1}$) combined with high transmission (90-95%) in the visible range nominate this material to be used as electrodes in solar cells and optoelectronic devices.

The used spray pyrolysis technique, has many advantages over the conventional techniques used in thin film preparation. It is simple, easy to construct and operate, needs no vacuum, and economic. It allows mass production of large area thin layer coatings at low cost.

Since the production of low cost solar cells is the long term objective, the spray pyrolysis technique adopted in this work, as well as, the quality of the prepared zinc oxide films are satisfactory candidates, for heterojunction solar cells.

CHAPTER I

INTRODUCTION

Zinc oxide is one of the transparent oxide semiconductors, which have wide band gap, so it allows high transmission in luminous solar range. Also, it could be doped to a level which makes the material metallic and hence it becomes infrared reflector and electrically highly conductive. The high interest in TCO coatings is due to their wide range of applications such as:

1. Heat-mirror suitable for applications in solar photo-thermal conversion and smart windows.
2. Heterojunction of TCO on bulk semiconductor shows considerable promise for use in low cost solar cells such as ZnO/CdTe.
3. The refractive index is in the right range so it could be used as anti-reflection coating on silicon.

Zinc oxide is an n-type semiconductor, due to the existence of non-intentionally impurities. Its band gap is 3.3 eV and its conductivity can be controlled over several decades, by doping. It has been a material of technological significance, in many fields, for centuries. The constituent elements are abundant and the material lends itself to a variety of thin-film deposition